## Product Summary

| $BV_{DSS}$ | $R_{DS(ON)}$ | $I_D$ $T_A$ = +25°C |
|---|---|---|
| 100V | 700mΩ @ $V_{GS}$ = 10V | 0.70A |
| | 900mΩ @ $V_{GS}$ = 6.0V | 0.62A |

## Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.

## Features and Benefits

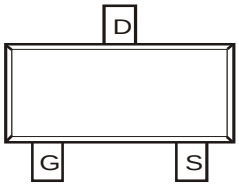
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

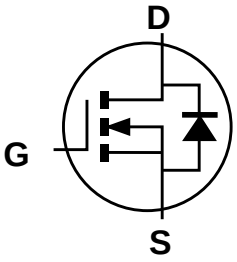
- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish Annealed over Alloy 42 Leadframe). (e3)
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)



Top View




Top View
Pin Configuration



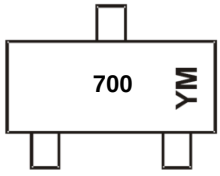

Equivalent Circuit

## Ordering Information (Note 4)

| Part Number | Case | Packaging |
|---|---|---|
| DMN10H700S-7 | SOT23 | 3,000/Tape & Reel |
| DMN10H700S-13 | SOT23 | 10,000/Tape & Reel |

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## Marking Information




700 = Product Type Marking Code
YM = Date Code Marking
Y or $\overline{Y}$ = Year (ex: E= 2017)
M = Month (ex: 9 = September)

Date Code Key

| Year | 2015 | 2016 | 2017 | 2018 | 2019 | 2020 | 2021 | 2022 | 2023 | 2024 | 2025 |
|---|---|---|---|---|---|---|---|---|---|---|---|
| Code | C | D | E | F | G | H | I | J | K | L | M |

| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|---|---|---|---|---|---|---|---|---|---|---|---|---|
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | O | N | D |


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## Maximum Ratings (@$T_A$ = +25°C, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Unit |
|---|---|---|---|---|---|
| Drain-Source Voltage | | | $V_{DSS}$ | 100 | V |
| Gate-Source Voltage | | | $V_{GSS}$ | ±20 | V |
| Continuous Drain Current (Note 6) $V_{GS}$ = 10V | Steady State | $T_A$ = +25°C<br>$T_A$ = +70°C | $I_D$ | 0.70<br>0.56 | A |
| Pulsed Drain Current (10µs Pulse, Duty Cycle ≦1%) | | | $I_{DM}$ | 2.5 | A |
| Maximum Body Diode Continuous Current (Note 6) | | | $I_S$ | 0.6 | A |

## Thermal Characteristics (@$T_A$ = +25°C, unless otherwise specified.)

| Characteristic | | Symbol | Value | Unit |
|---|---|---|---|---|
| Total Power Dissipation | (Note 5) | $P_D$ | 0.4 | W |
| | (Note 6) | | 0.5 | |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady state | $R_{\theta JA}$ | 303 | °C/W |
| Thermal Resistance, Junction to Ambient (Note 6) | | $R_{\theta JA}$ | 239 | |
| Thermal Resistance, Junction to Case | (Note 6) | $R_{\theta JC}$ | 88 | |
| Operating and Storage Temperature Range | | $T_J$, $T_{STG}$ | -55 to +150 | °C |

## Electrical Characteristics (@$T_A$ = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS (Note 7)** | | | | | | |
| Drain-Source Breakdown Voltage | $BV_{DSS}$ | 100 | — | — | V | $V_{GS}$ = 0V, $I_D$ = 250µA |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | — | — | 1 | µA | $V_{DS}$ = 100V, $V_{GS}$ = 0V |
| Gate-Source Leakage | $I_{GSS}$ | — | — | ±100 | nA | $V_{GS}$ = ±20V, $V_{DS}$ = 0V |
| **ON CHARACTERISTICS (Note 7)** | | | | | | |
| Gate Threshold Voltage | $V_{GS(TH)}$ | 2.0 | 2.7 | 4.0 | V | $V_{DS}$ = $V_{GS}$, $I_D$ = 250µA |
| Static Drain-Source On-Resistance | $R_{DS(ON)}$ | — | 540 | 700 | mΩ | $V_{GS}$ = 10V, $I_D$ = 1.5A |
| | | — | 550 | 900 | | $V_{GS}$ = 6.0V, $I_D$ = 1.0A |
| Diode Forward Voltage | $V_{SD}$ | — | 0.9 | 1.1 | V | $V_{GS}$ = 0V, $I_S$ = 1.5A |
| **DYNAMIC CHARACTERISTICS (Note 8)** | | | | | | |
| Input Capacitance | $C_{iss}$ | — | 235 | — | pF | $V_{DS}$ = 50V, $V_{GS}$ = 0V, f = 1.0MHz |
| Output Capacitance | $C_{oss}$ | — | 7 | — | | |
| Reverse Transfer Capacitance | $C_{rss}$ | — | 5 | — | | |
| Gate Resistance | $R_G$ | — | 1.9 | — | Ω | $V_{DS}$ = 0V, $V_{GS}$ = 0V, f = 1.0MHz |
| Total Gate Charge | $Q_g$ | — | 4.6 | — | nC | $V_{DS}$ = 50V, $V_{GS}$ = 10V, $I_D$ = 1.0A |
| Gate-Source Charge | $Q_{gs}$ | — | 1.1 | — | | |
| Gate-Drain Charge | $Q_{gd}$ | — | 1.6 | — | | |
| Turn-On Delay Time | $t_{D(ON)}$ | — | 2.5 | — | ns | $V_{DS}$ = 50V, $I_D$ = 1.0A, $V_{GS}$ = 10V, $R_G$ = 6.0Ω |
| Turn-On Rise Time | $t_R$ | — | 1.1 | — | | |
| Turn-Off Delay Time | $t_{D(OFF)}$ | — | 5.4 | — | | |
| Turn-Off Fall Time | $t_F$ | — | 1.0 | — | | |
| Reverse Recovery Time | $t_{RR}$ | — | 22 | — | ns | $V_R$ = 100V, $I_F$=1.8A, di/dt=100A/µs |
| Reverse Recovery Charge | $Q_{RR}$ | — | 15 | — | nC | |

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
7 .Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.


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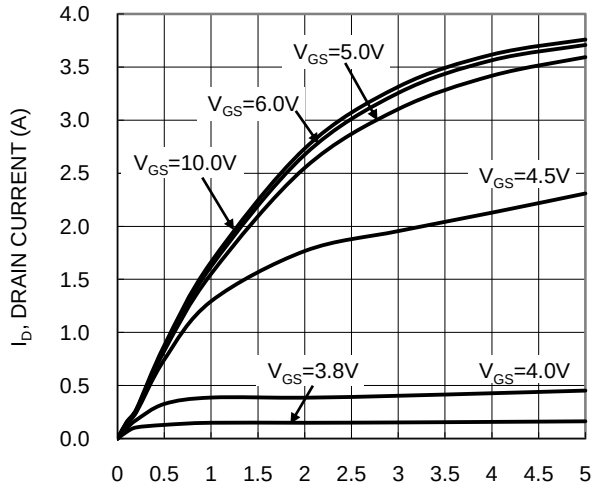



Figure 1. Typical Output Characteristic

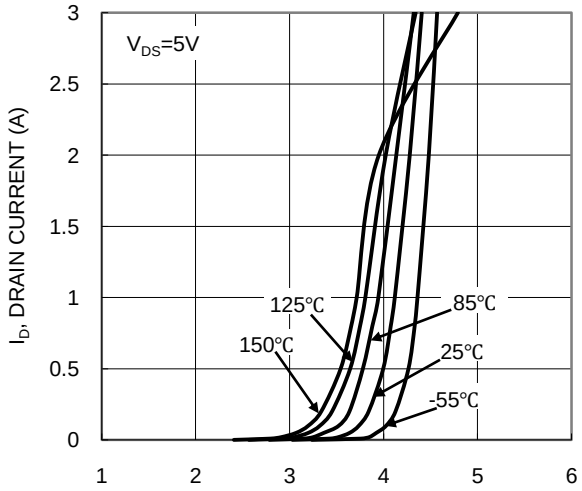



Figure 2. Typical Transfer Characteristic

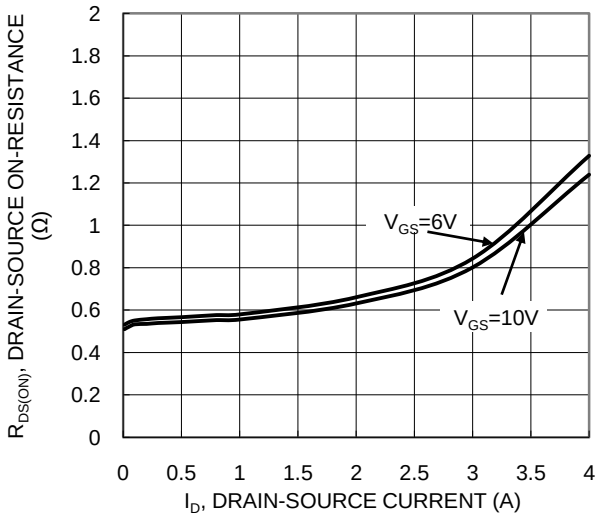



Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

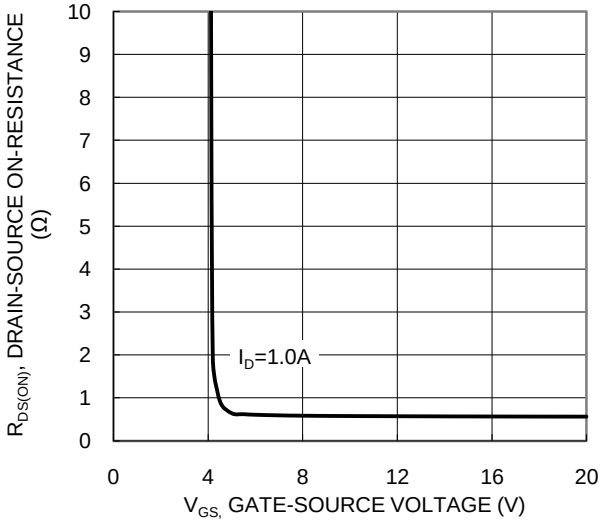



Figure 4. Typical Transfer Characteristic

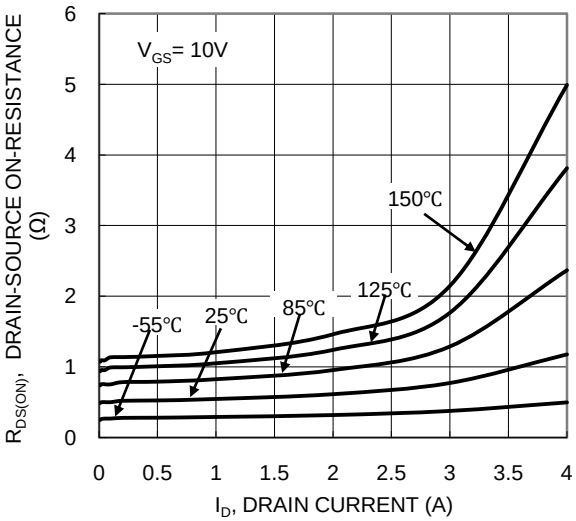



Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

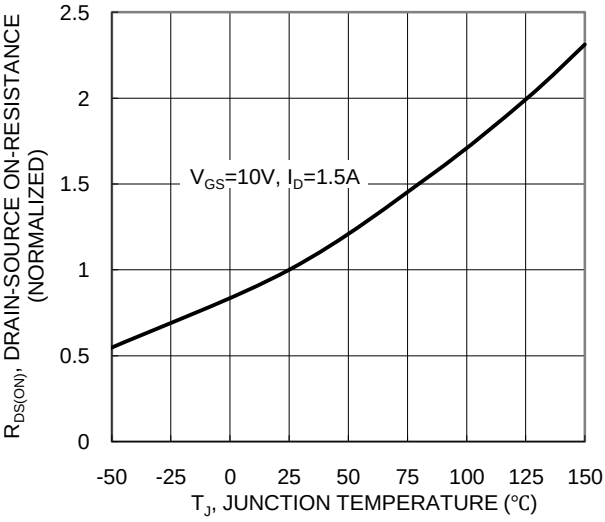



Figure 6. On-Resistance Variation with Junction Temperature


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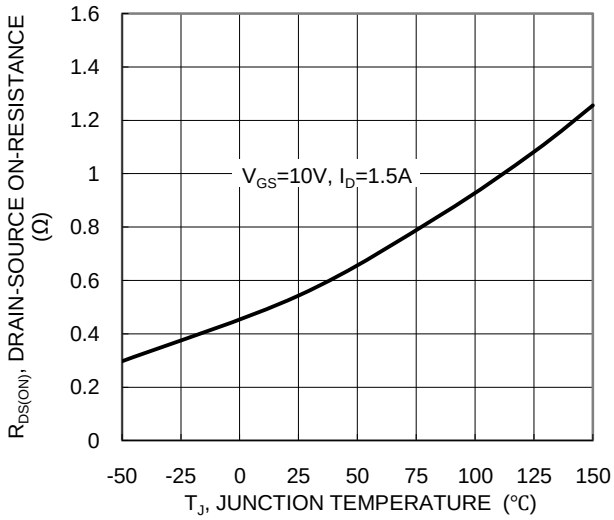



Figure 7. On-Resistance Variation with Junction Temperature

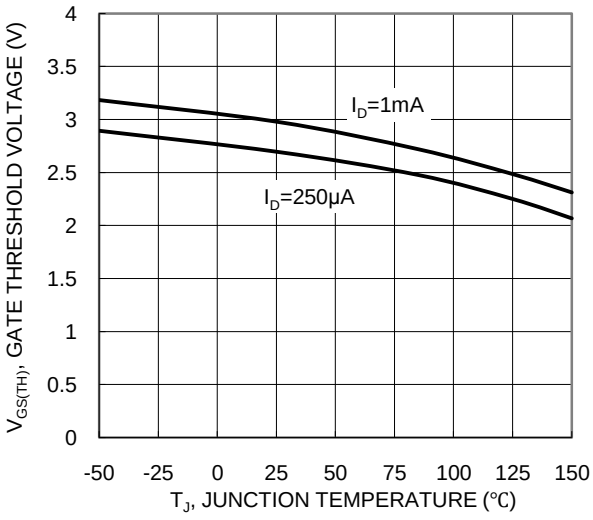



Figure 8. Gate Threshold Variation vs. Junction Temperature

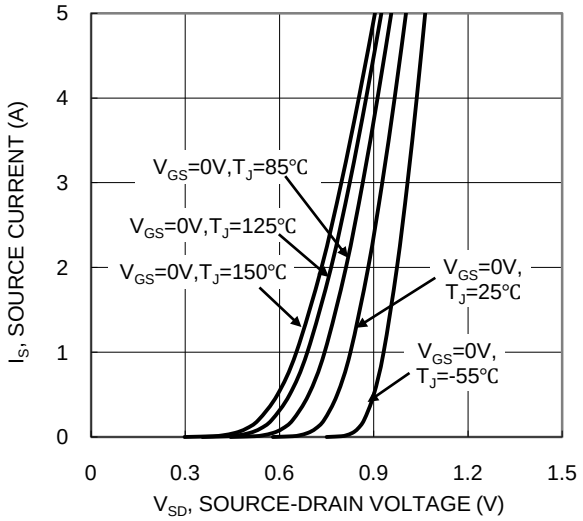



Figure 9. Diode Forward Voltage vs. Current

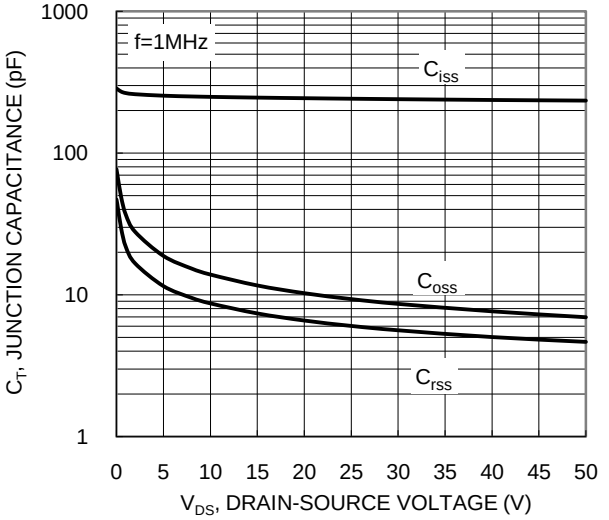



Figure 10. Typical Junction Capacitance

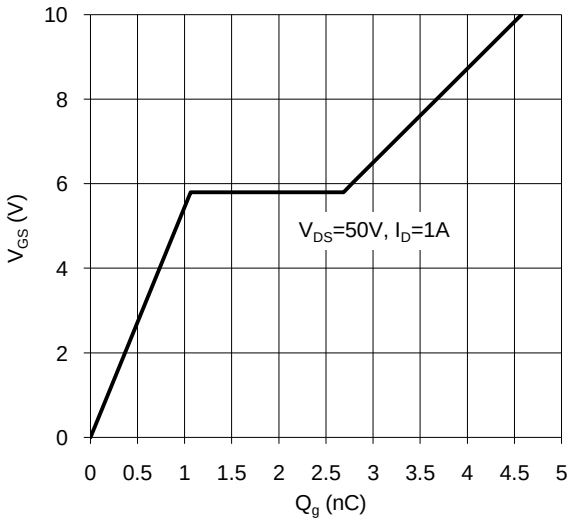



Figure 11. Gate Charge

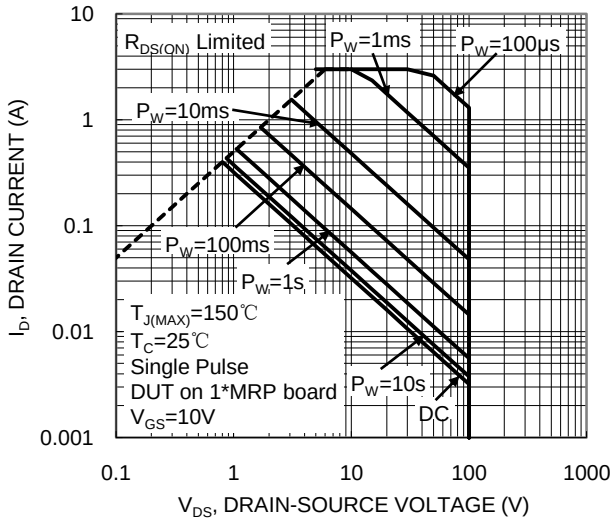



Figure 12. SOA, Safe Operation Area


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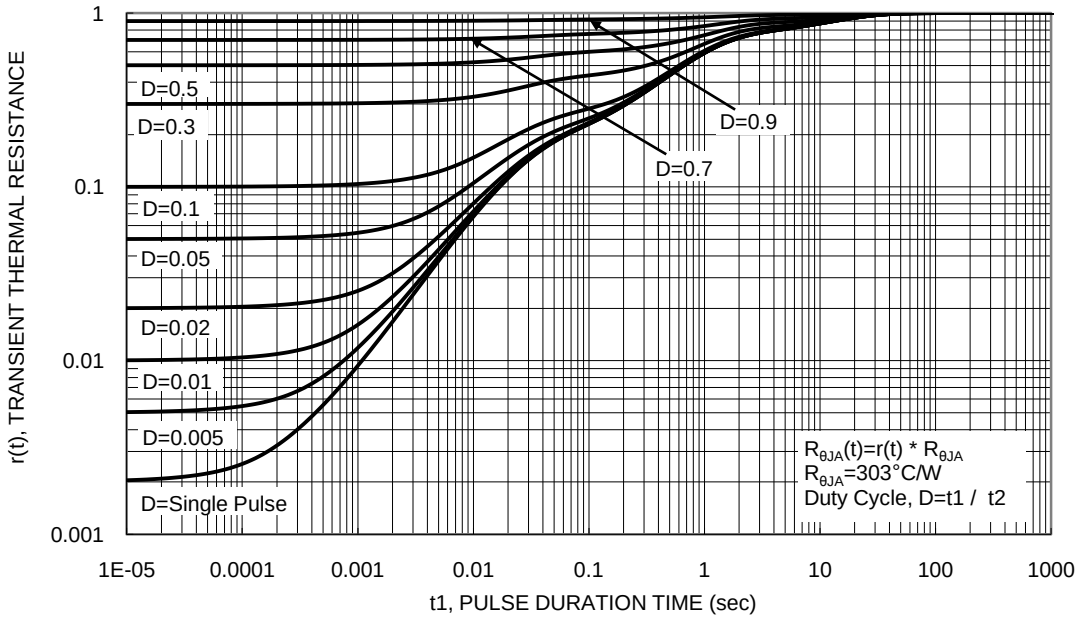


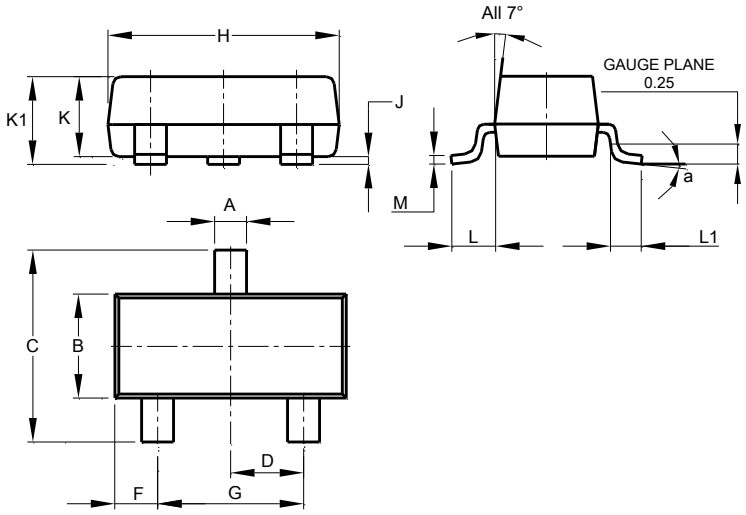

Figure 13. Transient Thermal Resistance


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## Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

**SOT23**

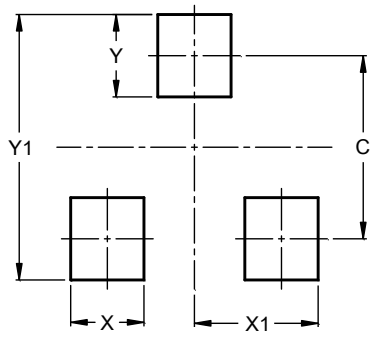



| SOT23 | | | |
|---|---|---|---|
| **Dim** | **Min** | **Max** | **Typ** |
| **A** | 0.37 | 0.51 | 0.40 |
| **B** | 1.20 | 1.40 | 1.30 |
| **C** | 2.30 | 2.50 | 2.40 |
| **D** | 0.89 | 1.03 | 0.915 |
| **F** | 0.45 | 0.60 | 0.535 |
| **G** | 1.78 | 2.05 | 1.83 |
| **H** | 2.80 | 3.00 | 2.90 |
| **J** | 0.013 | 0.10 | 0.05 |
| **K** | 0.890 | 1.00 | 0.975 |
| **K1** | 0.903 | 1.10 | 1.025 |
| **L** | 0.45 | 0.61 | 0.55 |
| **L1** | 0.25 | 0.55 | 0.40 |
| **M** | 0.085 | 0.150 | 0.110 |
| **a** | 0° | 8° | -- |
| **All Dimensions in mm** | | | |

## Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

**SOT23**




| Dimensions | Value (in mm) |
|---|---|
| **C** | 2.0 |
| **X** | 0.8 |
| **X1** | 1.35 |
| **Y** | 0.9 |
| **Y1** | 2.9 |


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